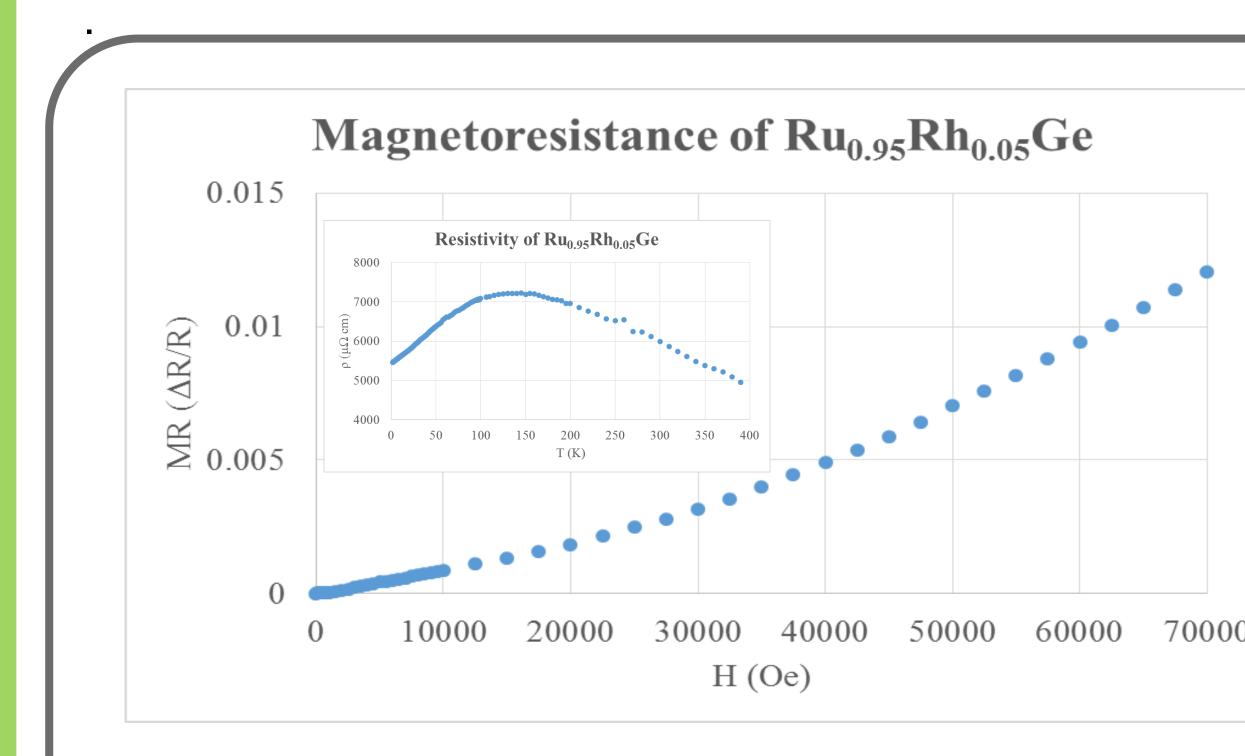
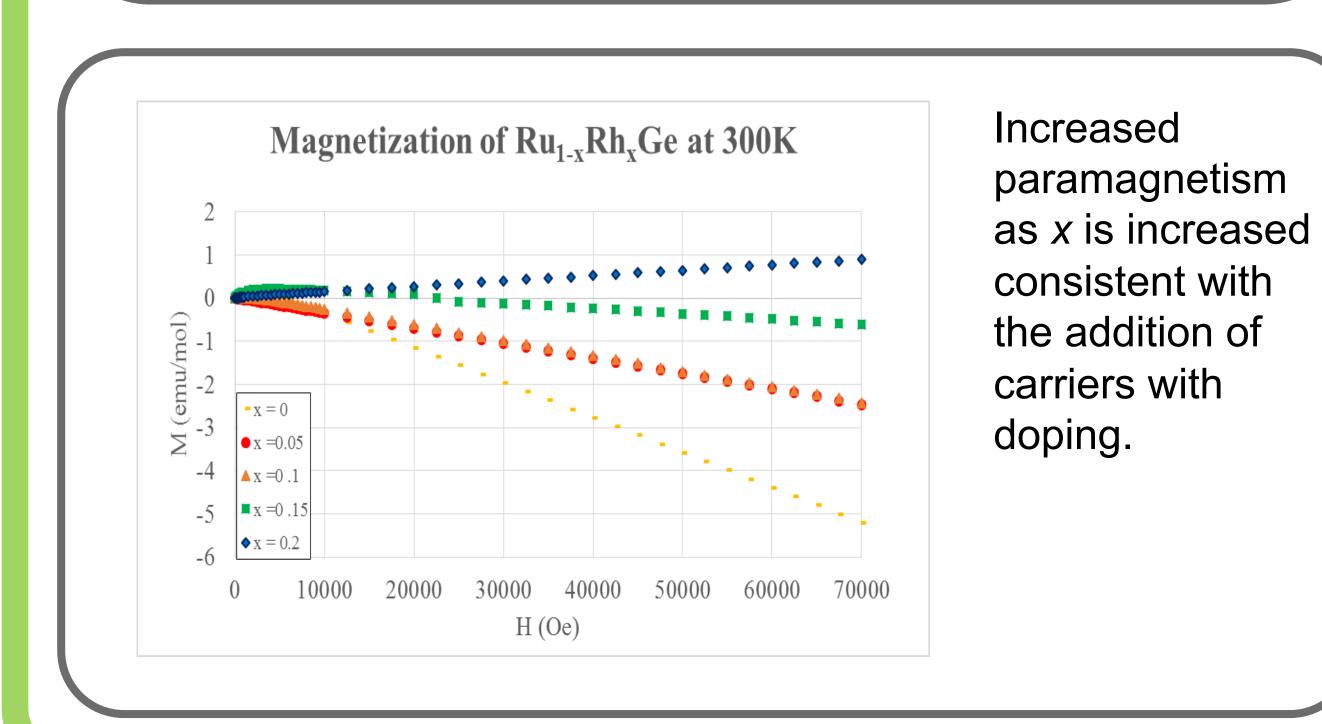


Abstract

Spin electronics, or spintronics, is thought to be an important future technology that will combine the logic and memory functions of processors into one nanoscale device. Spintronics will use magnetic semiconductors such as FeSi and RuGe that work as both a ferromagnetic material and a semiconductor. Spintronics has the potential to reduce heating, increase computing speed, reduce energy cost, and to reduce the size of logic elements. The idea in this project was to discover new magnetic semiconducting materials by doping small gap insulator RuGe with Fe and Rh. The samples were made by melting in an arc-furnace and/or the RF furnace followed by annealing at 1100 °C for 1 week. The magnetic susceptibility of our samples was measured at a field of 1 kOe at temperatures between 2 and 400 K. The magnetization was measured up to fields of 7 T at 2 and 300 K. Our data show a systematic increase in magnetic moment without signs of magnetic ordering for *x*<0.2. Resistivity and Magnetoresistance measurements are underway. Attempts to grow Ru_{1-x}Fe_xGe have been unsuccessful in producing single phase materials thus far.



A small positive magnetoresistance was measured at 10 K. The inset displays the resistivity from 2-400 K at zero field demonstrating weakly metallic behavior.



Exploring Rh and Fe Doped RuGe for a New Ferromagnetic Semiconductor

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simple cubic structure.

predicted by Tony Skyrme.

